

1 Binary-phase micrograting and polarization 2 beamsplitter for free-space micro-optical pickups

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Abstract. A pop-up binary-phase micrograting and a pop-up micro polarization beamsplitter, for potential use in micro-optical pickups, have been realized on a single silicon chip using a two-layer polysilicon and one-layer silicon nitride micromachining process. In the case of the micrograting, a diffraction efficiency ratio between 4 and 10 can be achieved provided that the duty cycle is between 0.4 and 0.6 and the depth between 455 and 485 nm, respectively. For a grating designed for a diffraction ratio of 7, the measured ratio is 8.31. The polarization beamsplitter is a silicon nitride thin film placed at the Brewster angle. The transmittance of the TM mode was measured to be more than 98.5%, while the reflectance of the TE mode was 21.4%. © 2007 Society of Photo-Optical Instrumentation Engineers. [DOI: 10.1117/1.2769362]

Subject terms: binary-phase grating; polarization beamsplitter; diffraction efficiency ratio; silicon nitride; optical pickup.

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37 1 Introduction

38 Microgratings and micro polarization beam splitters (PBSs)
39 are required in many micro-optical systems for sensing,
40 data storage, and signal processing where diffraction and
41 polarization states of light are of concern. In an optical data
42 storage system, a micrograting can be used to divide the
43 incident light into 0th-order and ± 1 st-order beams. The 0th-
44 order beam is used for reading and writing data, while the
45 ± 1 st-order beams are used for tracking servo control in the
46 three-beam tracking method. A PBS can be used to split the
47 light into two orthogonally polarized components, the
48 transverse electric (TE) and transverse magnetic (TM)
49 modes. The TM mode is for reading and writing the data on
50 the disk; the TE mode is used for monitoring the light in-
51 tensity.

52 Two silicon-based micromachining technologies have
53 drawn much attention for their high degree of accuracy and
54 monolithic integration with other optical components in
55 micro-optical pickups. One is based on surface-
56 micromachined microhinge technology; an out-of-plane,
57 three-dimensional micro-Fresnel lens,¹ a micrograting, a
58 micro-optical pickup,² a microetalon,³ and other elements
59 have been demonstrated. These elements used thin polysili-
60 con films as the optical patterns, which are not transparent
61 in the visible spectrum. The other technology is based on
62 bulk micromachining, which has been used to fabricate a
63 silicon nitride transmissive micrograting⁴ and a micro-
64 optical pickup system.⁵ These devices required a silicon
65 nitride layer as the mechanical substrate, which suffered
66 from reflection loss.

67 The objective of this paper is to fabricate a binary phase

micrograting and a micro-PBS, both of which are framed
by pop-up polysilicon structures for micro-optical pickup
operation in the visible spectrum. Low-stress silicon nitride
is used for its high transparency in the visible spectrum and
its superior chemical and mechanical properties.

2 Optical Design and Simulation

2.1 Binary-Phase Micrograting

To apply the micrograting in a micro-optical pickup, the
diffraction efficiency ratio η of the 0th-order beam intensity
 I_0 and the ± 1 st-order beam intensities $I_{\pm 1}$ should be controlled to the range from 4 to 10, depending on the requirement of the servo control system. In addition, the energy utilization efficiency, $\eta_u = (I_{-1} + I_0 + I_{+1}) / \sum I_l$, where $\sum I_l$ is the total intensity of the diffracted beams, should be as high

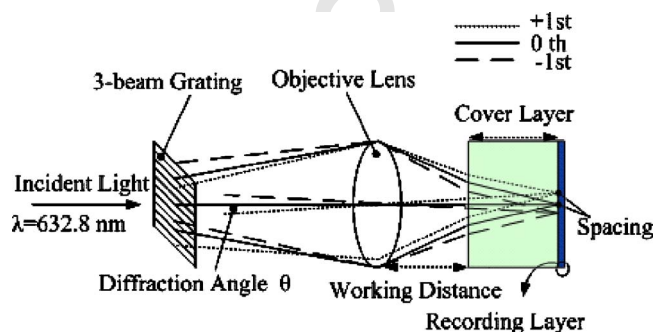


Fig. 1 Schematic of the three beams from a micrograting used for reading and tracking a disk. The working distance, the thickness of the cover layer, and the spacing between the diffraction beams on the disk determine the first-order diffraction angle θ , which is related to the period of the micrograting and to the wavelength of the incident light.

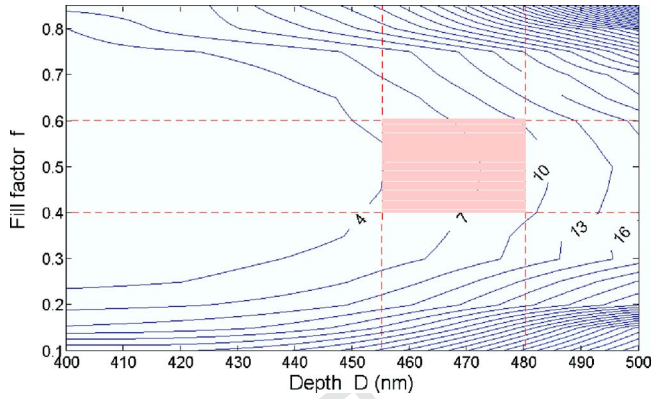


Fig. 2 Diffraction ratio ($I_0/I_{\pm 1}$) contours for various values of the fill factor f and of the grating depth D . The shaded rectangle represents diffraction ratios between 4 and 10. If the grating period is $8\ \mu\text{m}$ and linewidth is $4\ \mu\text{m}$, the process margins of f and D are as high as 0.5 ± 0.1 and $467.5 \pm 12.5\ \text{nm}$, respectively.

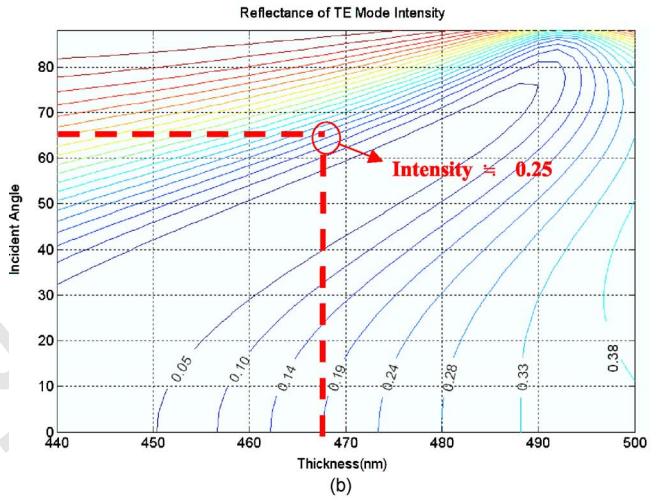
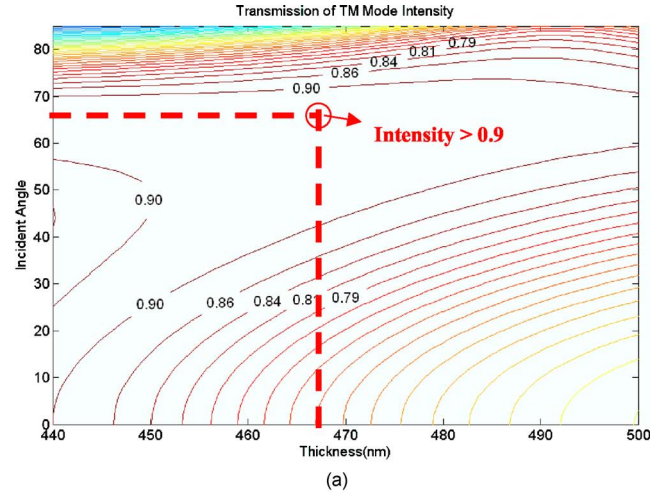


Fig. 3 Contours of (a) transmittance of the TM mode and (b) reflectance of the TE mode versus incident angle and thickness of silicon nitride. The intersection point of the dashed lines corresponds to the light incident on the micro-PBS with a thickness $467.5\ \text{nm}$ at the Brewster angle $\theta_B = 66\ \text{deg}$. Under this condition, the transmission of the TM mode intensity is larger than 90%, while the reflectance of the TE mode is about 25%.

82 as possible.⁶ The diffraction angle is determined by the op-
83 tical system layout parameters, such as the working dis-
84 tance, the thickness of the cover layer of the disk, and the
85 spacing between the 0th-order beam and the ± 1 st-order
86 beams on the disk, as shown in Fig. 1.

87 To determine the diffraction angle of the first-order
88 beams, the current design assumed $40\text{-}\mu\text{m}$ spacing on the
89 disk. For a $200\text{-}\mu\text{m}$ -thick cover layer with refractive index
90 1.6, the equivalent air thickness of the cover layer is
91 $125\ \mu\text{m}$. If the working distance between the objective lens
92 and the cover layer is $400\ \mu\text{m}$, then under the thin-lens
93 approximation for the objective lens, the diffraction angle θ
94 is about $4.35\ \text{deg}$. For a transmissive grating with θ
95 $= 4.35\ \text{deg}$, $m=1$, and $\lambda=632.8\ \text{nm}$, the period Λ is about
96 $8.35\ \mu\text{m}$, derived from the equation $\Lambda \times \sin \theta = m \times \lambda$. Here
97 $\Lambda = 8\ \mu\text{m}$ was selected in the design. To meet the specifi-
98 cation, namely $\eta=4$ to 10 and high η_u for $\Lambda=8\ \mu\text{m}$, a
99 grating with rectangular shape was designed using the com-
100 mercial software G-Solver.

101 The diffraction energy distribution of a grating can be
102 determined from the period, the linewidth, and the depth of
103 the grating, denoted by Λ , w , and D , respectively. The fill
104 factor, $f=w/\Lambda$, is defined as the ratio of the linewidth to the
105 grating period. Plane waves are incident normal to the grat-
106 ing, which is supported by a polysilicon frame. Low-stress
107 silicon nitride is used as the grating material, with refrac-
108 tive index $n=2.102+0.008i$ at $\lambda=632.8\ \text{nm}$.

109 It is found that when the fill factor is 0.50, multiple
110 grating depths may be selected. For example, $108\ \text{nm}$ (η_u
111 $=81.7\%$), $473\ \text{nm}$ ($\eta_u=83\%$), and $665\ \text{nm}$ ($\eta_u=74.7\%$)
112 satisfy $\eta=7:1$, which is the middle value of the specifi-
113 cation. Other grating depths meeting the requirement are
114 higher than $1000\ \text{nm}$, which is not suitable in surface mi-
115 cromachining processes. To have sufficient mechanical
116 strength and reasonable fabrication yield, the depth $473\ \text{nm}$
117 was selected, which also yields high energy utilization ef-
118 ficiency. The contour plot of the diffraction ratio $I_0/I_{\pm 1}$ is
119 shown in Fig. 2 for several values of D and f . A diffraction
120 ratio between 4 and 10 is obtained provided that $0.4 < f$
121 < 0.6 and $455\ \text{nm} < D < 480\ \text{nm}$. If the grating period is

$8\ \mu\text{m}$ and the linewidth is $4\ \mu\text{m}$, the process margins of f 122
and D are as high as 0.5 ± 0.1 and $467.5 \pm 12.5\ \text{nm}$, respec- 123
tively. 124

2.2 Thin-Film PBS 125

In a micro-optical pickup, the design target of the micro- 126
PBS is to have maximum transmittance of the TM mode 127
and detectable reflectance of the TE mode. The operation 128
principle of the thin-film PBS is based on the polarization- 129
dependent characteristics of the dielectric film,⁷ which can 130
be described by the characteristic matrix 131

$$M = \begin{bmatrix} B \\ C \end{bmatrix} = \begin{bmatrix} \cos \delta_i & -\frac{i}{\eta_i} \sin \delta_i \\ -i \eta_i \sin \delta_i & \cos \delta_i \end{bmatrix} \begin{bmatrix} 1 \\ \eta_a \end{bmatrix}, \quad (1)$$

where 132
133

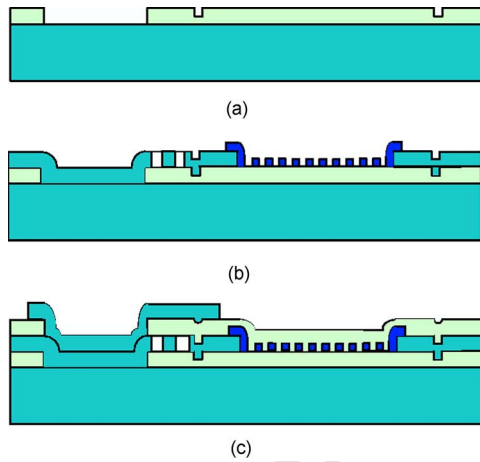


Fig. 4 Fabrication process flow of the micrograting and the micro-PBS. (a) The first dimple etch and anchor etch after the first silicon dioxide deposition. (b) Low-stress silicon nitride patterning after the first polysilicon deposition and patterning. (c) The second polysilicon deposition and patterning after the second silicon dioxide deposition and the second anchor etch.

134
$$\delta_i = \frac{2\pi}{\lambda} N_i d_i \cos \theta_i. \quad (2)$$

135 Here δ_i is related to the complex refractive index N_i , the
 136 thickness d_i of the layer, the wavelength λ , and the refrac-
 137 tive angle θ_i . The optical admittances η_i of the layer and η_a
 138 of the air substrate are given by

139
$$\eta_i = N_i \cos \theta_i \quad \text{for TE mode}, \quad (3)$$

140
$$\eta_a = \cos \theta_a \quad \text{for TE mode}, \quad (4)$$

141
$$\eta_i = N_i / \cos \theta_i \quad \text{for TM mode}, \quad (5)$$

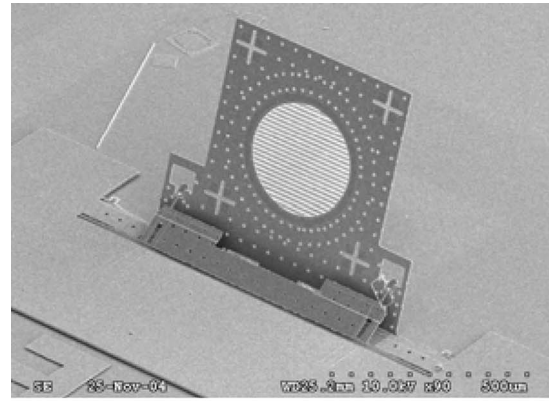
142
$$\eta_a = 1 / \cos \theta_a \quad \text{for TM mode}. \quad (6)$$

143 The reflectance R and transmittance T of the incident light
 144 for both polarizations can be derived from Eqs. (1) to (6):

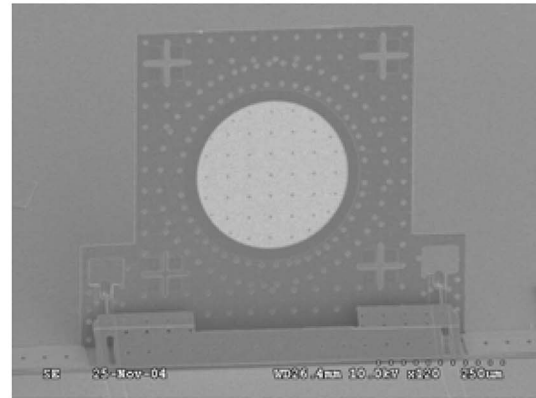
145
$$R = \left(\frac{\eta_a B - C}{\eta_a B + C} \right)^2, \quad (7)$$

146
$$T = \frac{4 \eta_a R_e(\eta_a)}{(\eta_a B + C)(\eta_a B + C)^*}. \quad (8)$$

147 The transmittance of the TM mode and the reflectance of
 148 the TE mode, therefore, are functions of the thickness of
 149 the silicon nitride film and incident angle, as shown in Fig.
 150 3(a) and 3(b). At the Brewster incidence angle, θ_B
 151 $= \tan^{-1} n_f$, the TM polarization will totally transmit, leaving
 152 the reflected light to be pure TE polarization. For a refrac-
 153 tive index $n_f = 2.1$ at $\lambda = 632.8$ nm, θ_B is about 66 deg. For a
 154 film thickness of 440 to 500 nm, the transmission of TM
 155 mode intensity is larger than 90% within $\theta_B \pm 10$ deg, while
 156 the reflectance of the TE mode varies significantly. In order
 157 to fabricate the micrograting and the micro-PBS on a single
 158 chip, the target thickness of the micro-PBS was 467.5 nm,



(a)



(b)

Fig. 5 SEM of a pop-up (a) micrograting and (b) micro-PBS. The sizes of the micrograting and micro-PBS are $500 \times 600 \mu\text{m}^2$ each. A pair of microspring latches is used to fix the microdevices nearly vertically. The optical pattern is circular with a diameter of $300 \mu\text{m}$.

the same as the grating. Under this condition, the reflectance of the TE mode is about 25%, which is small but acceptable in a practical system. The transmitted beam includes TE and TM modes. This large amount of transmitted TE mode will constitute noise; the minor-polarization crosstalk should be sufficiently low in some nonpolarized memory systems such as CD, DVD, and Blu-ray; however, it would be a problem in a polarized (e.g., a magneto-optical) memory system.

3 Fabrication

The micrograting and micro-PBS consist of low-stress silicon nitride mounted on a perpendicular polysilicon supporting frame. The measured tensile stress of the silicon nitride layer is about 50 MPa, which is low enough for optical applications.

The pop-up micrograting and micro-PBS were fabricated using the two-layer polysilicon and one-layer silicon nitride surface micromachining process shown in Fig. 4. To fabricate the devices, dimples and anchors were patterned in the sacrificial oxide layer [Fig. 4(a)]. After a microplate was formed in the structural polysilicon layer, the low-stress silicon nitride layer was patterned [Fig. 4(b)]. The second sacrificial oxide layer and structural polysilicon layer were deposited and patterned to implement the mi-

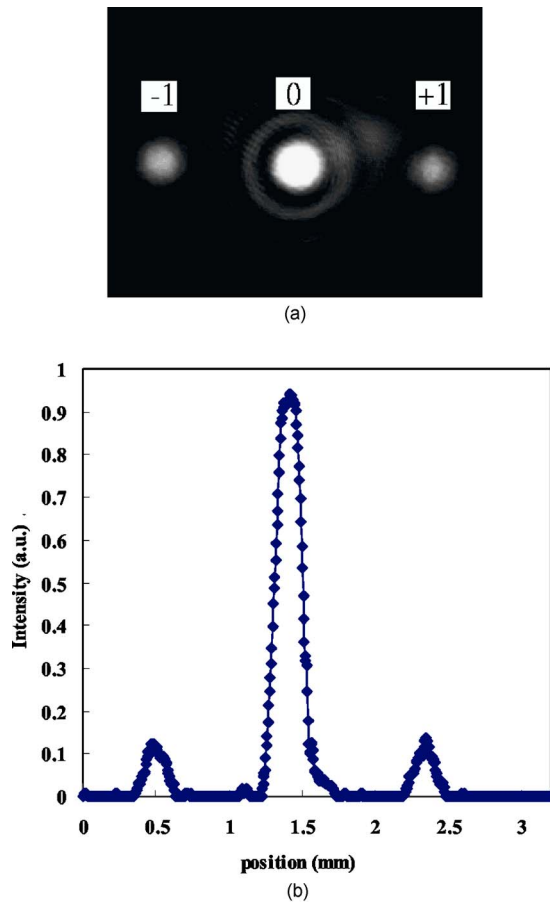


Fig. 6 (a) Diffraction pattern and (b) the cross section of its 0th-order beam and ± 1 st-order beams from the micrograting, measured by a CCD camera positioned 10 mm away.

183 crospring latches overlapping the microplate [Fig. 4(c)].
 184 After annealing and releasing, the micrograting and PBS
 185 were lifted to a vertical position by microprobes. Figure 5
 186 shows the SEM photograph of the pop-up grating and the
 187 pop-up PBS. The sizes of the micrograting and micro-PBS
 188 are $500 \times 600 \mu\text{m}^2$ each. A pair of microspring latches is
 189 used to fix the microdevices nearly vertically (at 92 deg).
 190 The aperture is circular with a diameter of $300 \mu\text{m}$.

191 4 Experimental Results and Discussion

192 To measure the optical performance of the micro devices, a
 193 He-Ne laser at $\lambda = 632.8 \text{ nm}$ was used as the light source. A
 194 polarizer was adjusted to obtain the required polarization
 195 states. The optical patterns were measured by a CCD cam-
 196 era positioned at 10 mm from each microdevice. For the
 197 micrograting, the measured Gaussian beam widths of the
 198 -1 st-, 0th-, and $+1$ st-order beams were 265, 290, and
 199 $270 \mu\text{m}$, respectively, indicating symmetrical intensity dis-
 200 tribution [Fig. 6(a)]. The measured diffraction angle at far
 201 field was 4.5 deg, which agrees well with the theoretical
 202 value of 4.53 deg. The measured diffraction efficiency ratio
 203 was 8.31 [Fig. 6(b)]. The deviation from the target value of
 204 7.0 was mainly due to the thickness variation and to the
 205 roughness of the sidewall and the surface of the grating.
 206 The mean roughness was 4.9 nm on average, which intro-
 207 duced phase variation and affected the energy distribution

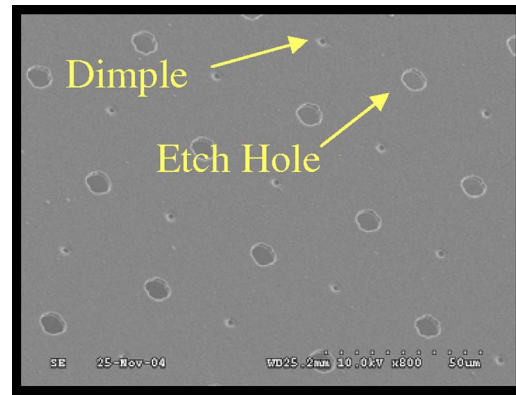


Fig. 7 SEM of etch holes and dimples in the micro-PBS. The actual shape of the two structures tends to be circular due to imperfect lithography and etching. The diameter of the etch hole is about $5 \mu\text{m}$.

of the diffracted beams. Under these conditions, the 208
 achieved η of 8.31 is well within the specification (4 to 10). 209
 The micrograting is thus applicable for a micro-optical 210
 pickup using the three-beam tracking method. 211

For the micro-PBS, the measured values of the transmit- 212
 tance of the TM mode and the reflectance of the TE mode 213
 at the Brewster angle were 98.5% and 21.4%, respectively. 214
 The deviation from the calculated values can be attributed 215
 to two factors: the existence of etch holes and dimples, and 216
 the thickness variation and roughness of the silicon nitride 217
 film. A close view of the micro-PBS with etch holes and 218
 dimples is shown in Fig. 7. The etch holes, which were 219
 used to release the microdevice from the substrate, reduce 220
 the reflection area by 1.5%. The dimples were used to avoid 221
 stiction between the microdevice and the substrate. Both 222
 structures also created higher-order diffraction beams and 223
 thus reduced the peak intensity of the main beams in the 224
 reflected light and the transmitted light, as shown in Fig. 8. 225
 The noises due to etch holes and dimples can be partly 226
 alleviated by randomly distributing the etch holes and 227
 dimples.⁸ A detailed description of the diffraction properties 228
 of surface-micromachined devices with etch holes can be 229
 found in Ref. 9. The thickness variation and roughness of 230
 the silicon nitride film as influenced by film growth and HF 231
 releasing can cause phase differences and scattering of the 232
 light at the interface. Besides, the thermal stress between 233
 the silicon nitride film and the polysilicon plate distorted 234
 the intensity profile of the main beam. 235

With spring latches, the pop-up angles of the micro- 236
 devices had a certain amount of deviation from 90 deg, 237
 which in turn affected the light incident angle and conse- 238
 quently the diffraction efficiency ratio and angular distribu- 239
 tion. To realize a micro-optical pickup, a more precise 240
 mechanism is required to assemble the microdevices on the 241
 substrate. 242

5 Conclusion 243

Using a two-layer polysilicon and one-layer low-stress sili- 244
 con nitride surface micromachining process, a binary phase 245
 pop-up micrograting and a micro-PBS were demonstrated. 246
 The size of the device is $500 \times 600 \mu\text{m}$ with an optical 247
 pattern area $300 \mu\text{m}$ in diameter. For the micrograting, the 248

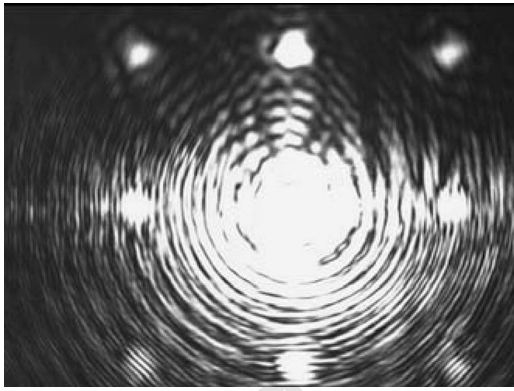


Fig. 8 CCD graph of the transmitted diffraction pattern from the micro-PBS. Higher-order diffraction beams are due to the existence of the periodic array of etch holes and dimples in the micro-PBS.

249 measured diffraction angle of 4.5 deg and diffraction effi-
250 ciency ratio of 8.31 agree reasonably with the designed
251 value. For the micro-PBS, the transmittance of the TM
252 mode and the reflectance of the TE mode reached 98.5%
253 and 21.4%, respectively. The optical performance of the
254 microdevices shows their potential for integration with
255 other micro-optical elements for optical storage applica-
256 tions.

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